

N-Channel 50 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)(Typ.)$	I _D (A) ^a	Q _g (Typ.)			
50	1.2 at V _{GS} = 10 V	0.31	1.7 nC			
30	1.4 at $V_{GS} = 4.5 \text{ V}$	0.31				

FEATURES

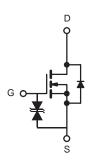
- DT-Trench Power MOSFET
- Surface Mount Package
- ESD Protection

Pb) RoHS

APPLICATIONS

- Battery operated systems
- Direct logic-level interface: TTL/CMOS

Top View Bottom View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	50	V		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current (T, = 150 °C)	T _A = 25 °C		0.31	А	
Continuous Drain Current (1) = 150 C)	T _A = 70 °C	— I _D	0.22		
Pulsed Drain Current	I _{DM}	1.55			
Maximum Dawar Dissipation 8	T _A = 25 °C	В	0.36	W	
Maximum Power Dissipation ^a	T _A = 70 °C	$ P_D$	0.22	v v	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^b	R _{thJA}	355	°C/W		

Notes

- a. $T_C = 25$ °C.
- b. Surface mounted on 1" x 1" FR4 board.

Rev. 1. 0



PARAMETER SYMB		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	50	-	-	>	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.8	-	2	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 10	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 240 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	0.31	-	-	Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 0.45 \text{ A}$	-	1.2	1.8	Ω	
	' 'DS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 0.25 \text{ A}$	-	1.4	2		
Forward Transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 0.1 A	-	0.5	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	23	40	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1MHz$	-	12	19		
Reverse Transfer Capacitance	C _{rss}		-	5	10		
Total Gate Charge ^c	Q_g		-	1.7	2.5	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 0.1 A	-	0.4	0.6		
Gate-Drain Charge ^c	Q_{gd}		-	0.45	0.8	1	
Switching Parameters							
Turn-On Delay Time	t _{d(on)}		-	8.6	-		
Rise Time	t _r	$V_{DS} = 30 \text{ V}, I_D = 0.2 \text{ A},$	-	4	-	l	
Turn-Off DelayTime	t _{d(off)}	$VGS = 10 \text{ V}, Rg = 3.5 \Omega$	-	23	-	ns	
Fall Time	t _f		-	14	-		
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)		·			
Continuous Source Current	Continuous Source Current I_S $T_C = 25^{\circ}$		-	-	0.31	Α	
Pulsed Source Current	I _{SM}		-	-	1.55	Α	
Forward Voltage ^a	V_{SD}	I _S = 0.2 A, V _{GS} = 0 V	-	-	1.2	V	

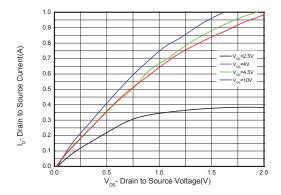
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

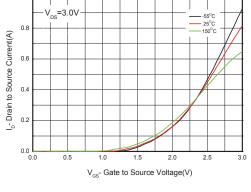
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



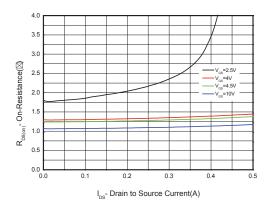
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



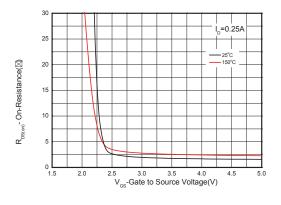
Output characteristics



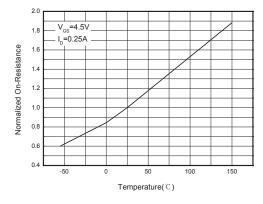
Transfer characteristics



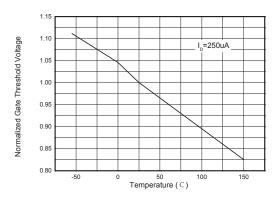
On-Resistance vs. Drain current



On-Resistance vs. Gate-to-Source voltage



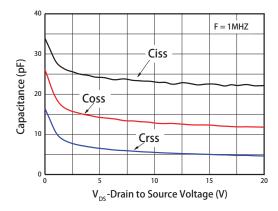
On-Resistance vs. Junction temperature



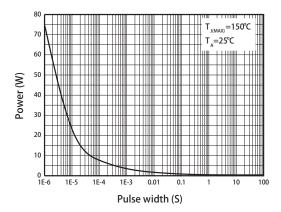
Threshold voltage vs. Temperature



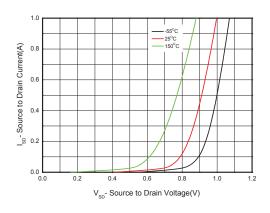
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



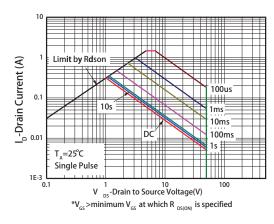
Capacitance



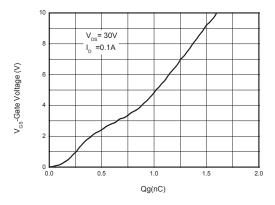
Single pulse power



Body diode forward voltage



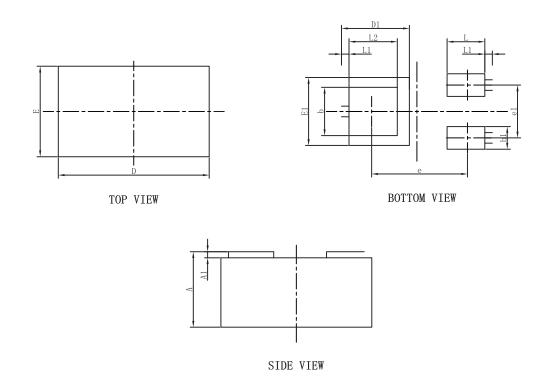
Safe operating power



Gate charge Characteristics



DFN1006-3L PACKAGEOUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	0.400	0.500	0.600
A1	0.000	0.050	0.150
D	0.850	1.000	1.150
Е	0.450	0.600	0.750
D1	0.450REF		
E1	0.450REF		
b	0.200	0.350	0.600
bl	0.050	0.150	0.250
e	0.635REF		
el	0.200	0.300	0.500
L	0.150	0.250	0.350
L1	0.050REF		
L2	0.150	0.300	0.400



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